

Section 4.2.4 Data Sheets

Zener Voltage Regulator Diodes

Section 4.2.4.1 Axial Leaded

SECTION 4.2.4.1.1 500 mW DO-35 GLASS

4

4.2

DATA SHEETS

Devices	Page No.
General Data — 500 mW DO-35 Glass	4-2-22
1N746A thru 1N759A, 1N957B thru 1N992B, 1N4370A thru 1N4372A	4-2-28
1N4678 thru 1N4717	4-2-30
1N5221B thru 1N5281B	4-2-31
1N5985B thru 1N6025B	4-2-33
BZX55C2V4 thru BZX55C91	4-2-34
BZX79C2V4 thru BZX79C200	4-2-35
BZX83C2V7 thru BZX83C33, M-ZPD2 7 thru M-ZPD33	4-2-36
MZ4099 thru MZ4104, MZ4614 thru MZ4627	4-2-37
MZ5520B thru MZ5530B	4-2-38

MULTIPLE PACKAGE QUANTITY (MPQ) REQUIREMENTS

Package Option	Type No. Suffix	MPQ (Units)
Tape and Reel	RL, RL2(1)	5K
Tape and Ammo	TA, TA2(1)	5K
Radial Tape and Reel	RR1, RR2(2)	3K
Radial Tape and Ammo	RA1, RA2(2)	3K

NOTES 1 The "2" suffix refers to 26 mm tape spacing
 2 The "1" suffix designates the cathode band is up and the cathode lead comes off first
 The "2" suffix indicates the cathode band is down and the anode lead comes off first

**MOTOROLA
SEMICONDUCTOR**

TECHNICAL DATA

**500 mW DO-35 Glass
Zener Voltage Regulator Diodes**

**GENERAL DATA APPLICABLE TO ALL SERIES IN
THIS GROUP**

**500 Milliwatt
Hermetically Sealed
Glass Silicon Zener Diodes**

Specification Features:

- Complete Voltage Range — 1.8 to 200 Volts
- DO-204AH Package — Smaller than Conventional DO-204AA Package
- Double Slug Type Construction
- Metallurgically Bonded Construction

Mechanical Characteristics:

CASE: Double slug type, hermetically sealed glass

MAXIMUM LEAD TEMPERATURE FOR SOLDERING PURPOSES: 230°C, 1/16" from case for 10 seconds

FINISH: All external surfaces are corrosion resistant with readily solderable leads

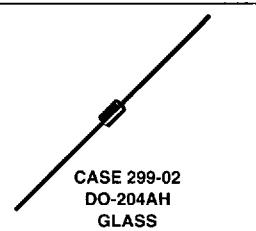
POLARITY: Cathode indicated by color band. When operated in zener mode, cathode will be positive with respect to anode

MOUNTING POSITION: Any

**GENERAL
DATA**

**500 mW
DO-35 GLASS**

**GLASS ZENER DIODES
500 MILLIWATTS
1.8-200 VOLTS**



4

4.2

MAXIMUM RATINGS (Motorola Devices)*

Rating	Symbol	Value	Unit
DC Power Dissipation and $T_L \leq 75^\circ\text{C}$ Lead Length = 3/8" Derate above $T_L = 75^\circ\text{C}$	P_D	500 4	mW mW/ $^\circ\text{C}$
Operating and Storage Temperature Range	T_J, T_{stg}	- 65 to +200	$^\circ\text{C}$

* Some part number series have lower JEDEC registered ratings

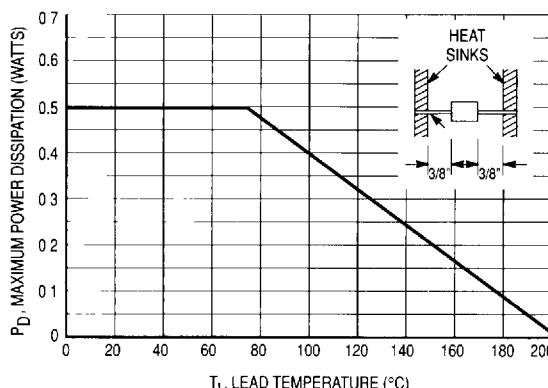


Figure 1. Steady State Power Derating

GENERAL DATA — 500 mW DO-35 GLASS

NOTE 1. SPECIAL SELECTIONS [†] AVAILABLE INCLUDE:

- a Nominal zener voltages between those shown
- b Nominal voltages at non-standard test currents

NOTE 2. TEMPERATURE COEFFICIENT (θ_{VZ})

Test conditions for temperature coefficient are as follows

Figure 4a $I_{ZT} = 7.5 \text{ mA}$, $T_1 = 25^\circ\text{C}$,

$T_2 = 125^\circ\text{C}$

Figure 4b, 4c I_{ZT} = Rated I_{ZT} (125 mW/ V_Z nom.)

$T_1 = 25^\circ\text{C}$, $T_2 = 125^\circ\text{C}$

Device to be temperature stabilized with current applied prior to reading breakdown voltage at the specified ambient temperature

NOTE 3. ZENER VOLTAGE (V_Z) MEASUREMENT

Nominal zener voltage is measured with the device junction in thermal equilibrium at the lead temperature of $30^\circ\text{C} \pm 1^\circ\text{C}$ and $3/8"$ lead length. Part number series that are pulse tested are so noted

NOTE 4. ZENER IMPEDANCE (Z_Z) DERIVATION

Z_{ZI} and Z_{ZD} are measured by dividing the ac voltage drop across the device by the ac current applied. The specified limits are for $I_Z(\text{ac}) = 0.1 I_Z(\text{dc})$ with the ac frequency = 60 Hz

[†] For more information on special selections contact your nearest Motorola representative

APPLICATION NOTE — ZENER VOLTAGE

Since the actual voltage available from a given zener diode is temperature dependent, it is necessary to determine junction temperature under any set of operating conditions in order to calculate its value. The following procedure is recommended:

Lead Temperature, T_L , should be determined from:

$$T_L = \theta_{LA} P_D + T_A.$$

θ_{LA} is the lead-to-ambient thermal resistance ($^\circ\text{C}/\text{W}$) and P_D is the power dissipation. The value for θ_{LA} will vary and depends on the device mounting method. θ_{LA} is generally 30 to $40^\circ\text{C}/\text{W}$ for the various clips and tie points in common use and for printed circuit board wiring.

The temperature of the lead can also be measured using a thermocouple placed on the lead as close as possible to the tie point. The thermal mass connected to the tie point is normally large enough so that it will not significantly respond to heat surges generated in the diode as a result of pulsed operation once steady-state conditions are achieved. Using the measured value of T_L , the junction temperature may be determined by:

$$T_J = T_L + \Delta T_{JL}.$$

ΔT_{JL} is the increase in junction temperature above the lead temperature and may be found from Figure 2 for dc power:

$$\Delta T_{JL} = \theta_{JL} P_D.$$

For worst-case design, using expected limits of I_Z , limits of P_D and the extremes of $T_J(\Delta T_J)$ may be estimated. Changes in voltage, V_Z , can then be found from:

$$\Delta V = \theta_{VZ} T_J.$$

θ_{VZ} , the zener voltage temperature coefficient, is found from Figures 4 and 5.

Under high power-pulse operation, the zener voltage will vary with time and may also be affected significantly by the zener resistance. For best regulation, keep current excursions as low as possible.

Surge limitations are given in Figure 7. They are lower than would be expected by considering only junction temperature, as current crowding effects cause temperatures to be extremely high in small spots, resulting in device degradation should the limits of Figure 7 be exceeded.

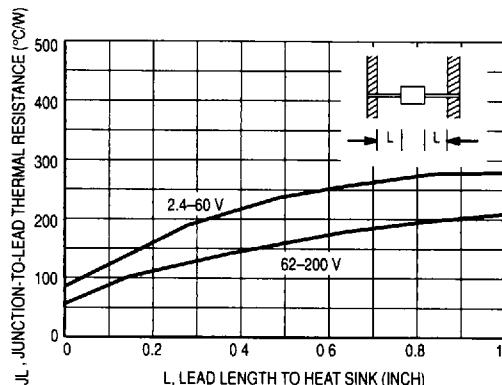


Figure 2. Typical Thermal Resistance

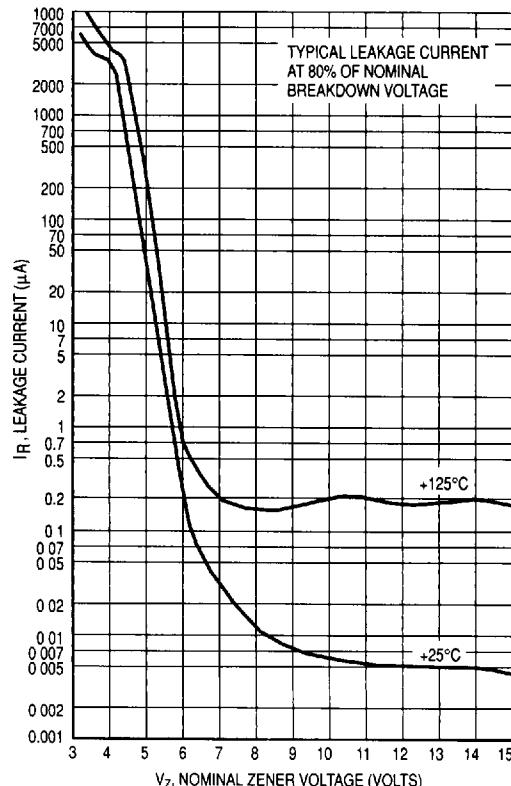
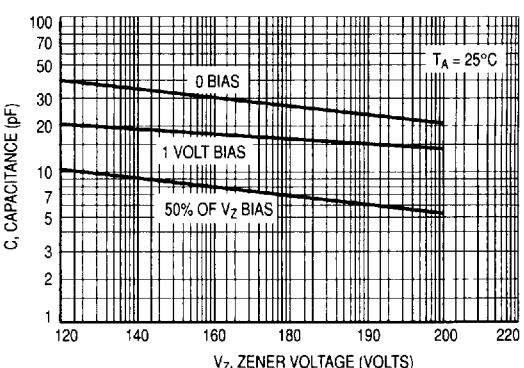
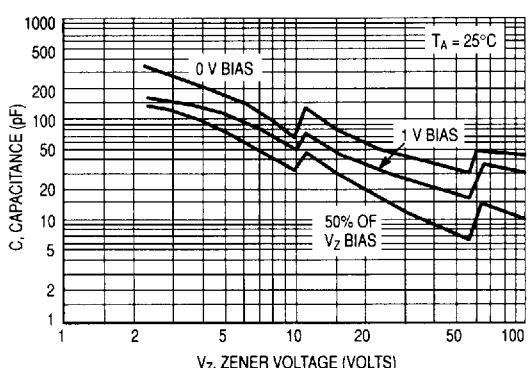
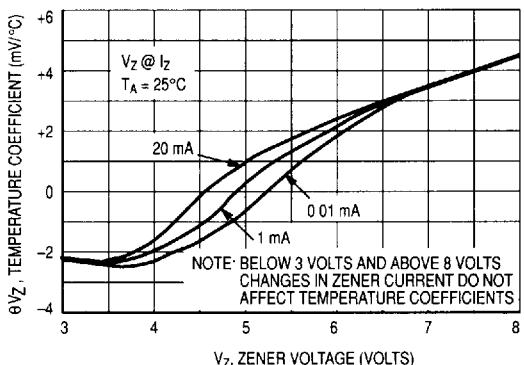
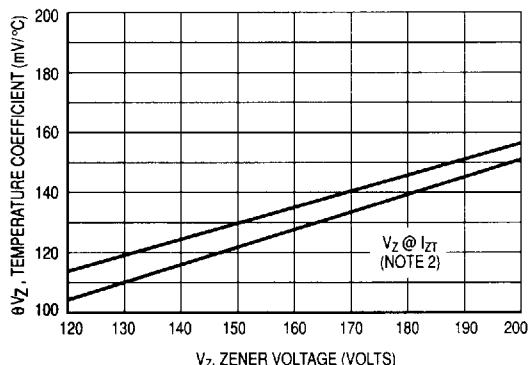
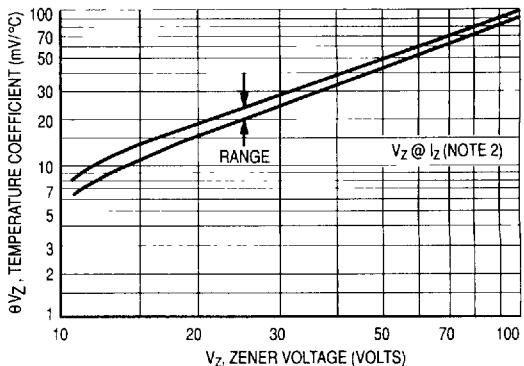
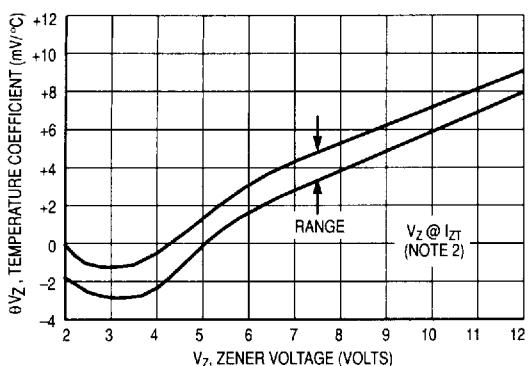


Figure 3. Typical Leakage Current

GENERAL DATA — 500 mW DO-35 GLASS

TEMPERATURE COEFFICIENTS

(-55°C to +150°C temperature range; 90% of the units are in the ranges indicated.)



GENERAL DATA — 500 mW DO-35 GLASS

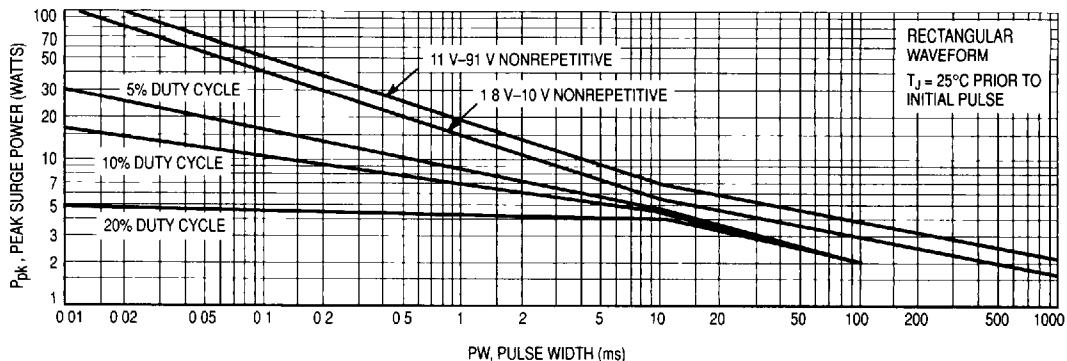


Figure 7a. Maximum Surge Power 1.8-91 Volts

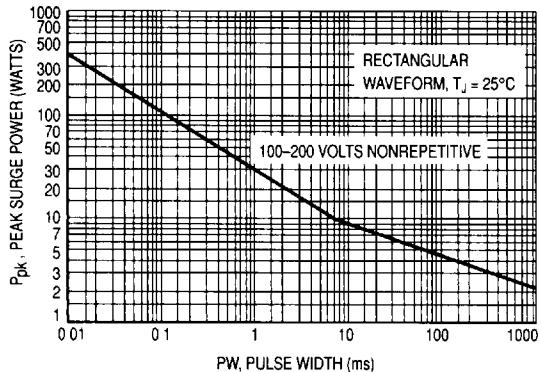
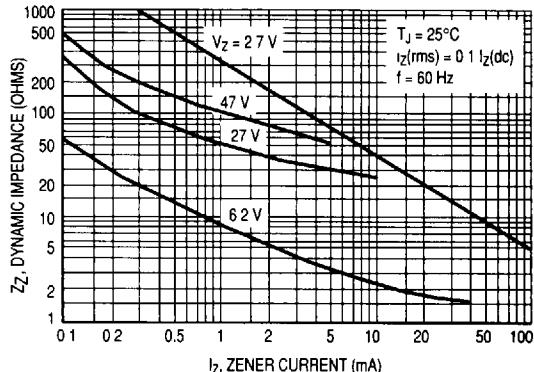
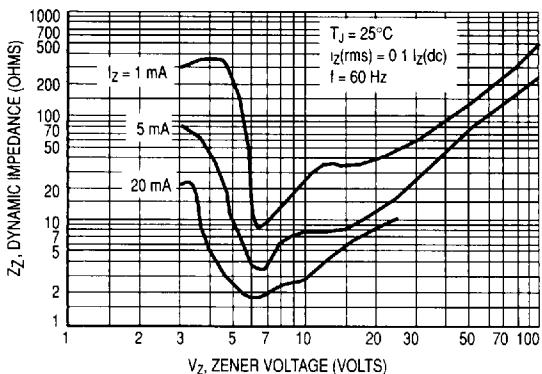
Figure 7b. Maximum Surge Power DO-204AH
100-200 VoltsFigure 8. Effect of Zener Current on
Zener Impedance

Figure 9. Effect of Zener Voltage on Zener Impedance

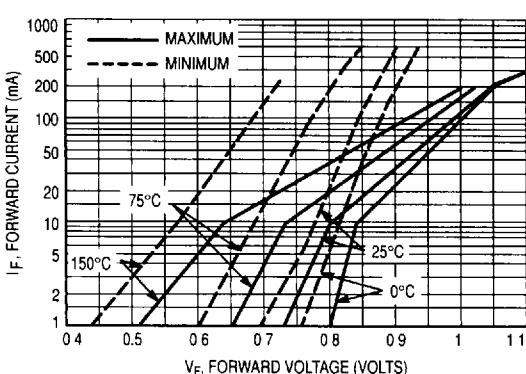


Figure 10. Typical Forward Characteristics

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4.2

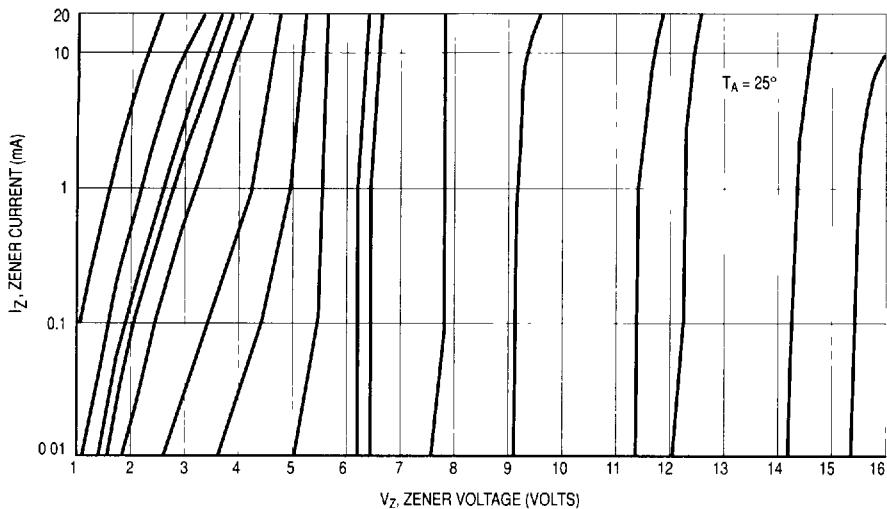
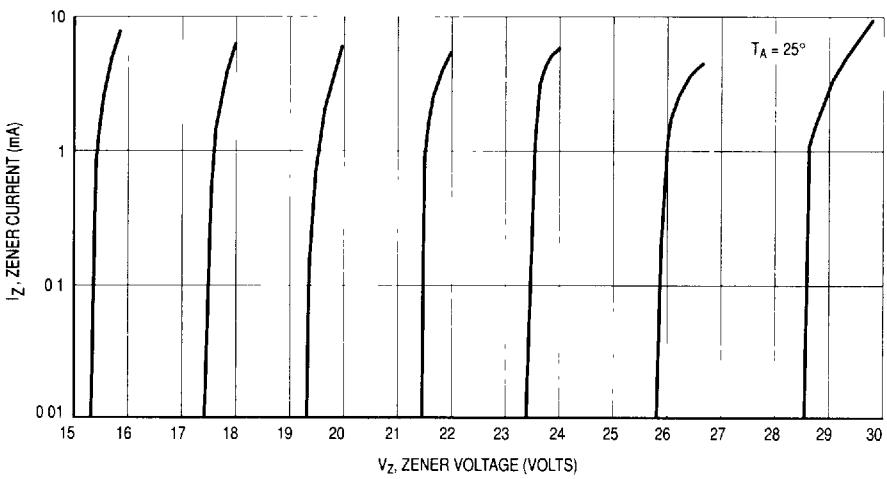


Figure 11. Zener Voltage versus Zener Current — V_Z = 1 thru 16 Volts

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4.2

Figure 12. Zener Voltage versus Zener Current — V_Z = 15 thru 30 Volts

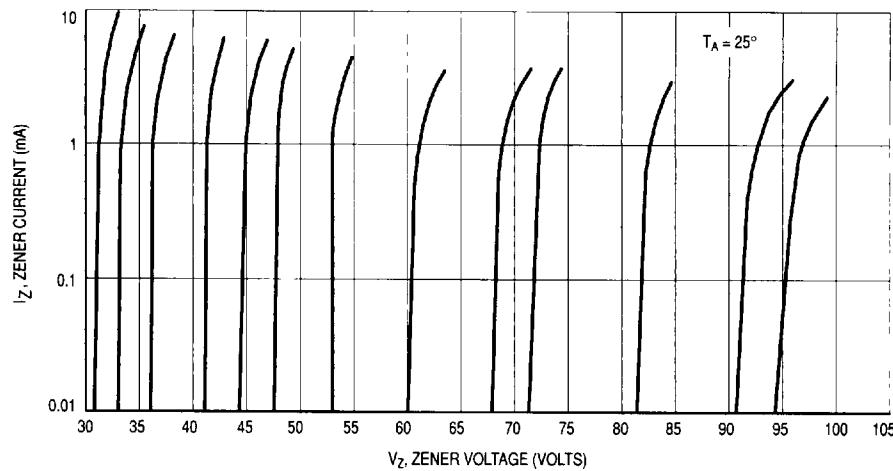
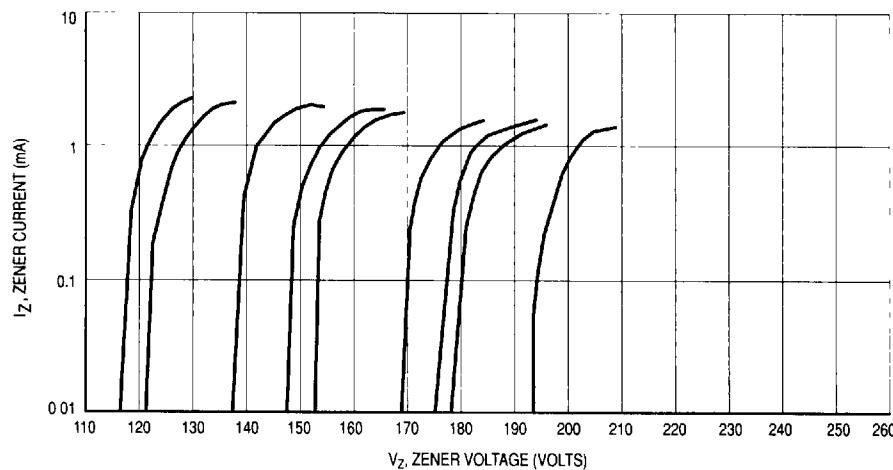
GENERAL DATA — 500 mW DO-35 GLASS

Figure 13. Zener Voltage versus Zener Current — V_Z = 30 thru 105 Volts

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4.2

Figure 14. Zener Voltage versus Zener Current — V_Z = 110 thru 220 Volts

1N746A thru 1N759A, 1N957B thru 1N992B, 1N4370A thru 1N4372A

MOTOROLA SC (DIODES/OPTO) 64E D ■ 6367255 0085399 9T6 ■ MOT7

Type Number (Note 1)	Nominal Zener Voltage V_z (Note 2) Volts	Test Current I_{ZT} mA	Maximum Zener Impedance (Note 3)			Maximum DC Zener Current I_{ZM} (Note 4) mA	Maximum Reverse Leakage Current	
			$Z_{ZT} @ I_{ZT}$ Ohms	$Z_{ZK} @ I_{ZK}$ Ohms	I_{ZK} mA		I_R Maximum μA	Test Voltage V_R
1N981B	68	1.8	230	2000	0.25	4.5	5	51.7
1N982B	75	1.7	270	2000	0.25	4.1	5	56
1N983B	82	1.5	330	3000	0.25	3.7	5	62.2
1N984B	91	1.4	400	3000	0.25	3.3	5	69.2
1N985B	100	1.3	500	3000	0.25	3	5	76
1N986B	110	1.1	750	4000	0.25	2.7	5	83.6
1N987B	120	1	900	4500	0.25	2.5	5	91.2
1N988B	130	0.95	1100	5000	0.25	2.3	5	98.8
1N989B	150	0.85	1500	6000	0.25	2	5	114
1N990B	160	0.8	1700	6500	0.25	1.9	5	121.6
1N991B	180	0.68	2200	7100	0.25	1.7	5	136.8
1N992B	200	0.65	2500	8000	0.25	1.5	5	152

NOTE 1. TOLERANCE AND VOLTAGE DESIGNATION

Tolerance Designation

The type numbers shown have tolerance designations as follows

1N4370A series $\pm 5\%$ units, C for $\pm 2\%$, D for $\pm 1\%$

1N746A series $\pm 5\%$ units, C for $\pm 2\%$, D for $\pm 1\%$

1N957B series $\pm 5\%$ units, C for $\pm 2\%$, D for $\pm 1\%$

NOTE 2. ZENER VOLTAGE (V_z) MEASUREMENT

Nominal zener voltage is measured with the device junction in thermal equilibrium at the lead temperature of $30^\circ\text{C} \pm 1^\circ\text{C}$ and $3/8"$ lead length

NOTE 3. ZENER IMPEDANCE (Z_z) DERIVATION

Z_{ZT} and Z_{ZK} are measured by dividing the ac voltage drop across the device by the ac current applied. The specified limits are for $I_z(\text{ac}) = 0.1 I_z(\text{dc})$ with the ac frequency = 60 Hz

NOTE 4. MAXIMUM ZENER CURRENT RATINGS (I_{ZM})

Values shown are based on the JEDEC rating of 400 mW. Where the actual zener voltage (V_z) is known at the operating point, the maximum zener current may be increased and is limited by the derating curve.

Low level oxide passivated zener diodes for applications requiring extremely low operating currents, low leakage, and sharp breakdown voltage.

- Zener Voltage Specified @ $I_{ZT} = 50 \mu A$
- Maximum Delta V_Z Given from 10 to 100 μA

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ C$, $V_F = 1.5 V$ Max at $I_F = 100 mA$ for all types)						
Type Number (Note 1)	Zener Voltage $V_Z @ I_{ZT} = 50 \mu A$ Volts			Maximum Reverse Current $I_R \mu A$ (Note 3)	Test Voltage V_R Volts	Maximum Zener Current I_{ZM} mA (Note 2)
	Nom (Note 1)	Min	Max			
1N4678	1.8	1.71	1.89	7.5	1	120
1N4679	2	1.9	2.1	5	1	110
1N4680	2.2	2.09	2.31	4	1	100
1N4681	2.4	2.28	2.52	2	1	95
1N4682	2.7	2.565	2.835	1	1	90
1N4683	3	2.85	3.15	0.8	1	85
1N4684	3.3	3.135	3.465	7.5	1.5	80
1N4685	3.6	3.42	3.78	7.5	2	75
1N4686	3.9	3.705	4.095	5	2	70
1N4687	4.3	4.085	4.515	4	2	65
1N4688	4.7	4.465	4.935	10	3	60
⇒ 1N4689	5.1	4.845	5.355	10	3	55
1N4690	5.6	5.32	5.88	10	4	50
1N4691	6.2	5.89	6.51	10	5	45
1N4692	6.8	6.46	7.14	10	5.1	35
1N4693	7.5	7.125	7.875	10	5.7	31.8
1N4694	8.2	7.79	8.61	1	6.2	29
1N4695	8.7	8.265	9.135	1	6.6	27.4
1N4696	9.1	8.645	9.555	1	6.9	26.2
1N4697	10	9.5	10.5	1	7.6	24.8
1N4698	11	10.45	11.55	0.05	8.4	21.6
1N4699	12	11.4	12.6	0.05	9.1	20.4
1N4700	13	12.35	13.65	0.05	9.8	19
1N4701	14	13.3	14.7	0.05	10.6	17.5
1N4702	15	14.25	15.75	0.05	11.4	16.3
1N4703	16	15.2	16.8	0.05	12.1	15.4
1N4704	17	16.15	17.85	0.05	12.9	14.5
1N4705	18	17.1	18.9	0.05	13.6	13.2
1N4706	19	18.05	19.95	0.05	14.4	12.5
1N4707	20	19	21	0.01	15.2	11.9
1N4708	22	20.9	23.1	0.01	16.7	10.8
1N4709	24	22.8	25.2	0.01	18.2	9.9
1N4710	25	23.75	26.25	0.01	19	9.5
1N4711	27	25.65	28.35	0.01	20.4	8.8
1N4712	28	26.6	29.4	0.01	21.2	8.5
1N4713	30	28.5	31.5	0.01	22.8	7.9
1N4714	33	31.35	34.65	0.01	25	7.2
1N4715	36	34.2	37.8	0.01	27.3	6.6
1N4716	39	37.05	40.95	0.01	29.6	6.1
1N4717	43	40.85	45.15	0.01	32.6	5.5

⇒ Preferred part

NOTE 1. TOLERANCE AND VOLTAGE DESIGNATION (V_Z)

The type numbers shown have a standard tolerance of $\pm 5\%$ on the nominal Zener voltage C for $\pm 2\%$, D for $\pm 1\%$

NOTE 2. MAXIMUM ZENER CURRENT RATINGS (I_{ZM})

Maximum Zener current ratings are based on maximum Zener voltage of the individual units and JEDEC 250 mW rating

NOTE 3. REVERSE LEAKAGE CURRENT (I_R)

Reverse leakage currents are guaranteed and measured at V_R as shown on the table

NOTE 4. MAXIMUM VOLTAGE CHANGE (ΔV_Z)

Voltage change is equal to the difference between V_Z at 100 μA and V_Z at 10 μA .

NOTE 5. ZENER VOLTAGE (V_Z) MEASUREMENT

Nominal Zener voltage is measured with the device junction in thermal equilibrium at the lead temperature at $30^\circ C +1^\circ C$ and 3/8" lead length

ELECTRICAL CHARACTERISTICS — continued ($T_A = 25^\circ\text{C}$ unless otherwise noted) Based on dc measurements at thermal equilibrium, lead length = 3/8"; thermal resistance of heat sink = 30°C/W) $V_F = 1\text{ Max}$ @ $I_F = 200\text{ mA}$ for all types

JEDEC Type No. (Note 1)	Nominal Zener Voltage $V_Z @ I_{ZT}$ Volts (Note 2)	Test Current I_{ZT} mA	Max Zener Impedance		Max Reverse Leakage Current		Max Zener Voltage Temperature Coeff. $\theta_{VZ} (\%/\text{ }^\circ\text{C})$ (Note 3)
			$Z_{ZT} @ I_{ZT}$ Ohms	$Z_{ZK} @ I_{ZK} = 0.25\text{ mA}$ Ohms	I_R μA	V_R Volts	
1N5266B	68	1.8	230	1600	0.1	52	+0.097
1N5267B	75	1.7	270	1700	0.1	56	+0.098
1N5268B	82	1.5	330	2000	0.1	62	+0.098
1N5269B	87	1.4	370	2200	0.1	68	+0.099
1N5270B	91	1.4	400	2300	0.1	69	+0.099
1N5271B	100	1.3	500	2600	0.1	76	+0.11
1N5272B	110	1.1	750	3000	0.1	84	+0.11
1N5273B	120	1	900	4000	0.1	91	+0.11
1N5274B	130	0.95	1100	4500	0.1	99	+0.11
1N5275B	140	0.9	1300	4500	0.1	106	+0.11
1N5276B	150	0.85	1500	5000	0.1	114	+0.11
1N5277B	160	0.8	1700	5500	0.1	122	+0.11
1N5278B	170	0.74	1900	5500	0.1	129	+0.11
1N5279B	180	0.68	2200	6000	0.1	137	+0.11
1N5280B	190	0.66	2400	6500	0.1	144	+0.11
1N5281B	200	0.65	2500	7000	0.1	152	+0.11

NOTE 1. TOLERANCE

The JEDEC type numbers shown indicate a tolerance of $\pm 5\%$. For tighter tolerance devices use suffixes "C" for $\pm 2\%$ and "D" for $\pm 1\%$.

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NOTE 2. SPECIAL SELECTIONS[†] AVAILABLE INCLUDE:

- 1 Nominal zener voltages between those shown
- 2 Nominal voltages at non-standard test currents

NOTE 3. TEMPERATURE COEFFICIENT (θ_{VZ})

Test conditions for temperature coefficient are as follows

- a $I_{ZT} = 7.5\text{ mA}$, $T_1 = 25^\circ\text{C}$,
 $T_2 = 125^\circ\text{C}$ (1N5221B through 1N5242B)
- b I_{ZT} = Rated I_{ZT} , $T_1 = 25^\circ\text{C}$,
 $T_2 = 125^\circ\text{C}$ (1N5243B through 1N5281B)

Device to be temperature stabilized with current applied prior to reading breakdown voltage at the specified ambient temperature

NOTE 4. ZENER VOLTAGE (V_Z) MEASUREMENT

Nominal zener voltage is measured with the device junction in thermal equilibrium at the lead temperature of $30^\circ\text{C} \pm 1^\circ\text{C}$ and 3/8" lead length

NOTE 5. ZENER IMPEDANCE (Z_Z) DERIVATION

Z_{ZT} and Z_{ZK} are measured by dividing the ac voltage drop across the device by the ac current applied. The specified limits are for $I_Z(\text{ac}) = 0.1 I_Z(\text{dc})$ with the ac frequency = 60 Hz

[†] For more information on special selections contact your nearest Motorola representative.

ELECTRICAL CHARACTERISTICS (at $T_A = 25^\circ\text{C}$)

Motorola ZPD and BZX83C series. Forward Voltage $V_F = 1$ Volt Max at $I_F = 50 \text{ mA}$

Device Type	Zener Voltage (Note 1) at $I_ZT = 5.0 \text{ mA}$			Impedance (Ω) Max (Note 2)			Typ. Temp. Coeff. at I_{ZT} % per $^\circ\text{C}$	V_R Min		
	Nominal	Min	Max	at I_{ZT}	BZX83	ZPD		BZX83	ZPD	at I_R
BZX83C2V7	ZPD2.7	2.7	2.5	2.9	85	600	500	-0.09	-0.04	100 μA
BZX83C3V0	ZPD3.0	3	2.8	3.2	90	600	500	-0.09	-0.03	60 μA
BZX83C3V3	ZPD3.3	3.3	3.1	3.5	90	600	500	-0.08	-0.03	30 μA
BZX83C3V6	ZPD3.6	3.6	3.4	3.8	90	600	500	-0.08...	-0.03	20 μA
BZX83C3V9	ZPD3.9	3.9	3.7	4.1	85	600	500	-0.07...	-0.03	10 μA
BZX83C4V3	ZPD4.3	4.3	4	4.6	80	600	500	-0.06	-0.01	5 μA
BZX83C4V7	ZPD4.7	4.7	4.4	5	78	600	500	-0.05	+0.02	2 μA
BZX83C5V1	ZPD5.1	5.1	4.8	5.4	60	550	480	-0.03	+0.04	100 nA
BZX83C5V6	ZPD5.6	5.6	5.2	6	40	450	400	-0.02	+0.06	100 nA
BZX83C6V2	ZPD6.2	6.2	5.8	6.6	10		200	-0.01	+0.07	100 nA
BZX83C6V8	ZPD6.8	6.8	6.4	7.2	8		150	+0.02	+0.07	3
BZX83C7V5	ZPD7.5	7.5	7	7.9	7		50	+0.03	+0.07	5
BZX83C8V2	ZPD8.2	8.2	7.7	8.7	7		50	+0.04	+0.07	6
BZX83C9V1	ZPD9.1	9.1	8.5	9.6	10		50	+0.05	+0.08	7
BZX83C10	ZPD10	10	9.4	10.6	15		70	+0.05	+0.08	7.5
BZX83C11	ZPD11	11	10.4	11.6	20		70	+0.05	+0.09	8.5
BZX83C12	ZPD12	12	11.4	12.7	20		90	+0.06	+0.09	9
BZX83C13	ZPD13	13	12.4	14.1	25		110	+0.07	+0.09	10
BZX83C15	ZPD15	15	13.8	15.6	30		110	+0.07...	+0.09	11
BZX83C16	ZPD16	16	15.3	17.1	40		170	+0.08...	+0.095	12
BZX83C18	ZPD18	18	16.8	19.1	50		170	+0.08	+0.10	100 nA
BZX83C20	ZPD20	20	18.8	21.2	55		220	+0.08	+0.10	100 nA
BZX83C22	ZPD22	22	20.8	23.3	55		220	+0.08	+0.10	100 nA
BZX83C24	ZPD24	24	22.8	25.6	80		220	+0.08	+0.10	100 nA
BZX83C27	ZPD27	27	25.1	28.9	80		250	+0.08	+0.10	100 nA
BZX83C30	ZPD30	30	28	32	80		250	+0.08	+0.10	100 nA
BZX83C33	ZPD33	33	31	35	80		250	+0.08	+0.10	100 nA

NOTE 1. Pulse test

NOTE 2. f = 1.0 kHz, $I_Z(\text{ac}) = 0.1 I_Z(\text{dc})$

... designed for 250 mW applications requiring low leakage, low impedance. Same as 1N4099 through 1N4104 and 1N4614 through 1N4627 except low noise test omitted.

- Voltage Range from 1.8 to 10 Volts
- Zener Impedance and Zener Voltage Specified for Low-Level Operation at $I_{ZT} = 250 \mu A$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ C$ unless otherwise specified. $I_{ZT} = 250 \mu A$ and $V_F = 1 V$ Max @ $I_F = 200 mA$ for all types)

Type Number (Note 1)	Nominal Zener Voltage V_Z (Note 2) (Volts)	Max Zener Impedance Z_{ZT} (Note 3) (Ohms)	Max Reverse Current I_R (μA)	@ (Note 5)	Test Voltage V_R (Volts)	Max Zener Current I_{ZM} (Note 4) (mA)
MZ4614	1.8	1200	7.5		1	120
MZ4615	2	1250	5		1	110
MZ4616	2.2	1300	4		1	100
MZ4617	2.4	1400	2		1	95
MZ4618	2.7	1500	1		1	90
MZ4619	3	1600	0.8		1	85
MZ4620	3.3	1650	7.5		1.5	80
MZ4621	3.6	1700	7.5		2	75
MZ4622	3.9	1650	5		2	70
MZ4623	4.3	1600	4		2	65
MZ4624	4.7	1550	10		3	60
MZ4625	5.1	1500	10		3	55
MZ4626	5.6	1400	10		4	50
MZ4627	6.2	1200	10		5	45
MZ4099	6.8	200	10		5.2	35
MZ4100	7.5	200	10		5.7	31.8
MZ4101	8.2	200	1		6.3	29
MZ4102	8.7	200	1		6.7	27.4
MZ4103	9.1	200	1		7	26.2
MZ4104	10	200	1		7.6	24.8

NOTE 1. TOLERANCE AND VOLTAGE DESIGNATION

The type numbers shown have a standard tolerance of $\pm 5\%$ on the nominal zener voltage

NOTE 2. ZENER VOLTAGE (V_Z) MEASUREMENT

Nominal Zener Voltage is measured with the device junction in the thermal equilibrium with ambient temperature of $25^\circ C$

NOTE 3. ZENER IMPEDANCE (Z_{ZT}) DERIVATION

The zener impedance is derived from the 60 cycle ac voltage, which results when an ac current having an rms value equal to 10% of the dc zener current (I_{ZT}) is superimposed on I_{ZT}

NOTE 4. MAXIMUM ZENER CURRENT RATINGS (I_{ZM})

Maximum zener current ratings are based on maximum zener voltage of the individual units

NOTE 5. REVERSE LEAKAGE CURRENT I_R

Reverse leakage currents are guaranteed and are measured at V_R as shown on the table

NOTE 6. SPECIAL SELECTORS AVAILABLE INCLUDE:

- a) Nominal Zener voltages between those shown
- b) Tighter voltage tolerances. Contact your nearest Motorola representative for more information

Low Voltage Avalanche Passivated Silicon Oxide Zener Regulator Diodes

. . . Same as 1N5520B through 1N5530B except low noise test spec omitted.

- Low Maximum Regulation Factor
- Low Zener Impedance
- Low Leakage Current

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise specified Based on dc measurements at thermal equilibrium, $V_F = 1.1 \text{ Max } @ I_F = 200 \text{ mA for all types}$)								
Motorola Type No. (Note 1)	Nominal Zener Voltage $V_Z @ I_{ZT}$ Volts (Note 2)	Test Current I_{ZT} mAdc	Max Zener Impedance $Z_{ZT} @ I_{ZT}$ Ohms (Note 3)	Max Reverse Leakage Current		Maximum DC Zener Current I_{ZM} mAdc (Note 5)	Regulation Factor ΔV_Z Volts (Note 6)	Low V_Z Current I_{ZL} mAdc
				I_R μAdc (Note 4)	$V_R - \text{Volts}$			
MZ5520B	3.9	20	22	1	1	98	0.85	2.0
MZ5521B	4.3	20	18	3	1.5	88	0.75	2.0
MZ5522B	4.7	10	22	2	2	81	0.6	1.0
MZ5523B	5.1	5	26	2	2.5	75	0.65	0.25
MZ5524B	5.6	3	30	2	3.5	68	0.3	0.25
MZ5525B	6.2	1	30	1	5	61	0.2	0.01
MZ5526B	6.8	1	30	1	6.2	56	0.1	0.01
MZ5527B	7.5	1	35	0.5	6.8	51	0.05	0.01
MZ5528B	8.2	1	40	0.5	7.5	46	0.05	0.01
MZ5529B	9.1	1	45	0.1	8.2	42	0.05	0.01
MZ5530B	10	1	60	0.05	9.1	38	0.1	0.01

NOTE 1. TOLERANCE AND VOLTAGE DESIGNATION

The "B" suffix type numbers listed are $\pm 5\%$ tolerance of nominal V_Z .

NOTE 2. ZENER VOLTAGE (V_Z) MEASUREMENT

Nominal zener voltage is measured with the device junction in thermal equilibrium with ambient temperature of 25°C .

NOTE 3. ZENER IMPEDANCE (Z_Z) DERIVATION

The zener impedance is derived from the 60 Hz ac voltage, which results when an ac current having an rms value equal to 10% of the dc zener current (I_{ZT}) is superimposed on I_{ZT} .

NOTE 4. REVERSE LEAKAGE CURRENT I_R

Reverse leakage currents are guaranteed and are measured at V_R as shown on the table.

NOTE 5. MAXIMUM REGULATOR CURRENT (I_{ZM})

The maximum current shown is based on the maximum voltage of a $\pm 5\%$ type unit, therefore, it applies only to the "B" suffix device. The actual I_{ZM} for any device may not exceed the value of 400 milliwatts divided by the actual V_Z of the device.

NOTE 6. MAXIMUM REGULATION FACTOR (ΔV_Z)

ΔV_Z is the maximum difference between V_Z at I_{ZT} and V_Z at I_{ZL} measured with the device junction in thermal equilibrium.

NOTE 7. SPECIAL SELECTORS AVAILABLE INCLUDE:

- a) Nominal Zener voltages between those shown
- b) Tighter voltage tolerances Contact your nearest Motorola representative for more information